MJD148

NPN Silicon Power Transistor

DPAK For Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

Features

- High Gain 50 Min @ $I_C = 2.0 A$
- Low Saturation Voltage 0.5 V @ $I_C = 2.0 \text{ A}$
- High Current Gain Bandwidth Product f_T = 3.0 MHz Min @ I_C = 250 mAdc
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings: Human Body Model, 3B; >8000 V Machine Model, C; >400 V
- This is a Pb-Free Package

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	45	Vdc
Collector-Base Voltage	V _{CB}	45	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current - Continuous - Peak	IC	4.0 7.0	Adc
Base Current	Ι _Β	50	mAdc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	20 0.16	W W/°C
Total Power Dissipation (Note 1) @ T _A = 25°C Derate above 25°C	P _D	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	71.4	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 These ratings are applicable when surface mounted on the minimum pad sizes recommended.



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POWER TRANSISTOR 4.0 AMPERES 45 VOLTS, 20 WATTS

MARKING DIAGRAM



DPAK CASE 369C STYLE 1



A = Assembly Location

Y = Year

WW = Work Week

J148 = Device Code

G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MJD148T4	DPAK	2500/Tape & Reel
MJD148T4G	DPAK (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Test Conditions	Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage (Note 2)	I _C = 100 mAdc, I _B = 0	V _{CEO(sus)}	45	ı	Vdc
Collector Cutoff Current	V _{CB} = 45 Vdc, I _E = 0	І _{СВО}	ı	20	μAdc
Emitter Cutoff Current	V _{BE} = 5 Vdc, I _C = 0	I _{EBO}	-	1	mAdc
ON CHARACTERISTICS					
DC Current Gain (Note 2)	$\begin{split} I_C &= 10 \text{ mAdc, } V_{CE} = 5 \text{ Vdc} \\ I_C &= 0.5 \text{ Adc, } V_{CE} = 1 \text{ Vdc} \\ I_C &= 2 \text{ Adc, } V_{CE} = 1 \text{ Vdc} \\ I_C &= 3 \text{ Adc, } V_{CE} = 1 \text{ Vdc} \end{split}$	h _{FE}	40 85 50 30	- 375 - -	
Collector-Emitter Saturation Voltage (Note 2)	I _C = 2 Adc, I _B = 0.2 Adc	V _{CE(sat)}	-	0.5	Vdc
Base-Emitter On Voltage (Note 2)	I _C = 2 Adc, V _{CE} = 1 Vdc	V _{BE(on)}	-	1.1	Vdc
DYNAMIC CHARACTERISTICS					
Current-Gain-Bandwidth Product	I_C = 250 mAdc, V_{CE} = 1 Vdc, f = 1 MHz	f _T	3	-	MHz

^{2.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

TYPICAL CHARACTERISTICS

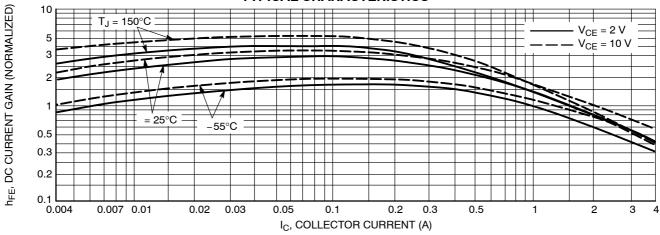


Figure 1. DC Current Gain

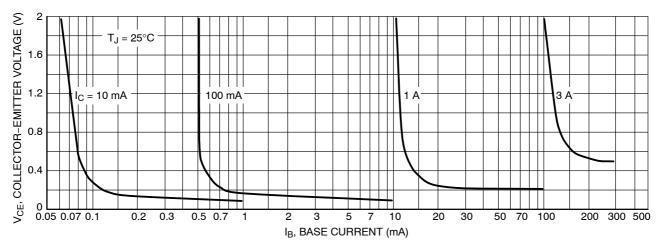


Figure 2. Collector Saturation Region

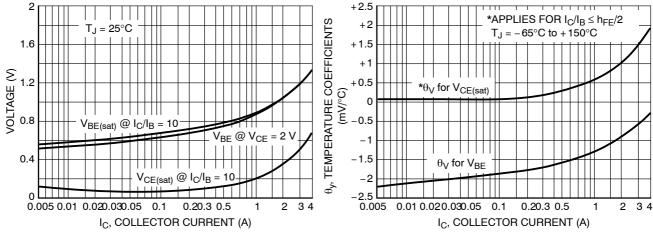


Figure 3. "On" Voltages

Figure 4. Temperature Coefficients

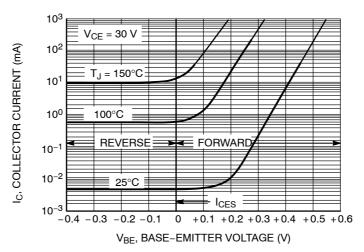


Figure 5. Collector Cut-Off Region

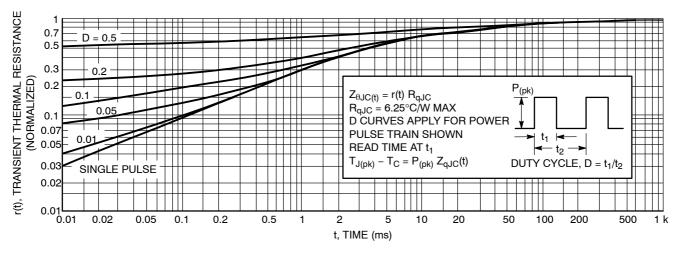


Figure 6. Thermal Response

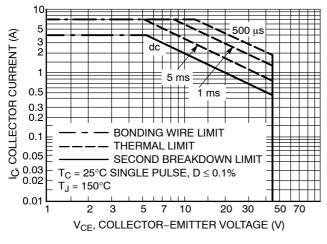


Figure 7. Maximum Rated Forward Bias

FORWARD BIAS SAFE OPERATING AREA INFORMATION

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

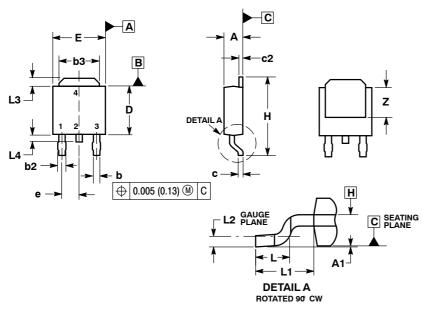
The data of Figure 7 is based on $T_{J(pk)} = 150^{\circ}\text{C}$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 6. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

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PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE)

CASE 369C-01 ISSUE D



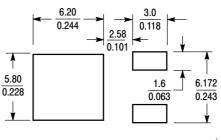
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES.

 - THERMAL PAD CONTOUR OPTIONAL WITHIN DI-MENSIONS b3, L3 and Z.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
 DIMENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY. DATUMS A AND B ARE DETERMINED AT DATUM

	INCHES MILLIMET			ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
Е	0.250	0.265	6.35	6.73
е	0.090 BSC		2.29	BSC
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108	0.108 REF		REF
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR

SOLDERING FOOTPRINT*



mm SCALE 3:1

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.